In this paper, we use high-resolution ARPES of ZnO (0001) together with resonant photoemission as a test of theoretical treatments for ZnO. We show that GW calculations based on GGA, GGA+ U, and HSE wave functions exhibit similar too-high (overestimation) Zd-

functional without further corrections due to quasiparticlemeasurements were taken, and the constant-energy contour energy shifts can be expected only if these shifts vanish for thelot in Fig. 1(b) exhibits hexagonal symmetry, reßecting respective functional.

## III. RESULTS AND DISCUSSION

ture of ZnO is shown in Fig.1. The arrows in Fig.1(a) depict the sliced directions in the-M-K plane where the

the hexagonal Brillouin zone of wurtzite ZnO. The VBM is located at the binding energy § 3.45 eV, and the Fermi level is approximately located near the bottom of conduction band due to oun-type Ga-doped ZnO. The valence bands A comparison of theoretical and experimental band strucobserved in the -K-M and -M- directions are highly dispersive, as can be seen in Fig(sc)D1(f). The ZnO valence band structure can be partitioned into three segments: (i) the O-p bands at $\S3.5 \text{ eV} < E_B < \S7.5 \text{ eV}$ , (ii) the Zns/O-p band atŠ7.5 eV < E B < Š9.5 eV, which is formed due to hybridization between the emptystates of the Z<sup>2</sup>t cation and the occupied states of the 🗗 anion, and (iii) the Zrd bands a§ 10 eV < E B < § 12 eV. The positions of Q- and Zn-d bands are conprmed experimentally by resonant photoemission (see Supplemental Material, Fig. 45th O-p states.

> Our results are in good agreement with previously reported work<sup>8</sup> for the Op bands. However, here, we use an ultraviolet

FIG. 1. (Color online)k scans in hexagonal plane of the ZnO Brillouin zone and comparison between experimental and theoretical band structure. A photon energy of 135 eV is chosen to study the -M-K basal plane. (a) The-M-K plane and (b) its constant-energy contour plot of the photoemission intensity. The red lines denote Brillouin zone boundaries, and the dashed blue lines are connectors to the points. The arrows indicate the sliced directions measured. (c) and (d) Comparison between experimental band structure (gray scale) and theoretical band structure within the GW(GGA) scheme. The origin of energy is chosen at the conduction band minimum. The red lines represent O-bands, the green lines hybridized ZhO-p bands, and the blue line Zohbands. It can be seen that the Zoband is too high, and there is overlap between **Z**/O-p and Znd bands. (e) and (f) Comparison between experimental band structure (gray scale) and theoretical band structure within the &W<sub>d</sub>(GGA+ U) scheme. The Znd-band is no longer too high, and the ZhO-p and Zn-d bands do not overlap. The horizontal dashed line indicates VBM energy. All the experimental band structures (energy distribution curves) shown here are second derivatives.

TABLE I. Comparison of different computational schemes of DFT and GW for ZnO. The initial DFT wave functions are calculated using the GGA, GGA+ U, or HSE functionals. The GW  $V_d$  with GGA+ U input scheme is used as a reference [cf. F1(s)] and1(f)]. Here, E  $_{VBM}$  is the GW quasiparticle energy shift with respect to the single-particle energies of the respective initial DFT functional. The experimental band gap for ZnO is 3.44 eV and band position (Fig1) is  $\check{S}$  7.50 eV.

	E <sub>g</sub> (DFT)	E <sub>g</sub> (GW)	E <sub>VBM</sub>	d band position from VBM
GW+ V <sub>d</sub> (GGA+ U)	1.52	3.30	Š 0.99	Š 7.45
GW(GGA)	0.80	2.92	Š 1.42	Š 6.26
GW(GGA+ U)	1.52	2.94	Š 0.63	Š 6.33
GW(HSE)	3.46	3.22	+ 0.70	Š 6.21

shows the band structures for GGA, GGAU, and HSE, and for each case the resulting GW(DFT) band structures. The GW+  $V_d$ (GGA+ U) result is shown here only as a reference for the experimental band energies [Fige) and1(f)]. There are several important observations: (1) The and energies in GW are overestimated by a similar amount for all three initial Hamiltonians. Also, the trend of an underestimated GW band gap exists for all three DFT functionals, which can be interpreted as due to the repulsion shifting the VBM upwards. (2) In the GGA calculation, the Zhbands are located at a very high energy and overlap with the

Zn-s/O-p band causing a spurious rr 0 TD -0.0004 Tc (bands)Tj -22.2675 -1.15 TD -0.00s TD -081o4idiz0 TD 354.65 0.As22.26

minimum) conbrmed the  $\phi$ -character. In addition, the relatively high intensity as well as the lack of intensity modulation at Š 10 eV < E  $_{\rm B}$  < 12 eV imply Znd character.

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<sup>&</sup>lt;sup>40</sup>P. Hohenberg and W. KohPhys. Rev. 136, B864 (1964), W. Kohn and L. J. Shamibid. 140, A1133 (1965).

 $<sup>^{41}</sup>See$  Supplemental Material <code>atttp://link.aps.org/supplemental/10.1103/PhysRevB.86.2351f6</code>r Fig. S1. Resonant photoemission of Op states at . The intensity modulation observed at Š 3.5 eV < E  $_{\rm B}$  < Š 7 eV (relative to conduction band